

**AMENDMENT**

**In the Claims:**

Please amend claim 20 as follows:

1-19. (Canceled)

20. (currently amended)      Structure comprising a thin layer (2) integral with a support, the thin layer (2) being a layer of conductive or semi-conductive material made insulating by ion implantation except for at least one zone (9) that allows a vertical electrical connection through the entire thickness of the thin layer (2) electrically connecting the support to a face of the thin layer opposite to the support, wherein said layer (2) and at least one zone (2) substantially have the same thickness.

21. (previously amended)      Structure according to Claim 20, characterized in that the thin layer comprises a multitude of said zones, said multitude of zones being distributed over the entire surface of the thin layer.

22. (previously amended)      Structure according to Claim 20, characterized in that the thin layer comprises one of said zone or a plurality of said zones concentrated to constitute at least one conductive path or at least one conductive track.

23. (previously amended)      Structure according to claim 20, characterized in that the thin layer (2) is made integral with the support (3) through an intermediate conductive interface.

24. (previously amended) Structure according to Claim 23, characterized in that said intermediate conductive interface is constituted by a metal layer.

25. (previously amended) Structure according to Claim 24, characterized in that said metal layer is a layer of palladium.

26. (previously amended) Structure according to claim 23, characterized in that deposition of conductive bonding materials is associated with said intermediate conductive interface.

27. (original) Structure according to Claim 26, characterized in that the conductive bonding materials are successive deposits of titanium, nickel and gold.

28. (previously amended) Structure according to claim 20, characterized in that the thin layer (2) is made integral with the support (3) through the use of a brazing material.

29. (original) Structure according to Claim 28, characterized in that the brazing material is based on indium.

30. (previously amended) Structure according to claim 20, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

31. (previously amended) Structure according to claim 23, characterized in that the support (3) is made of silicon.

32. (previously amended) Structure according to claim 22, characterized in that the thin layer (2) is made integral with the support (3) through an intermediate conductive interface.

33. (previously amended) Structure according to claim 25, characterized in that deposition of conductive bonding materials is associated with said metal layer.

34. (previously amended) Structure according to claim 22, characterized in that the thin layer (2) is made integral with the support (3) through the use of a brazing material.

35. (previously added) Structure according to claim 29, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

36. (previously added) Structure according to claim 29, characterized in that the support (3) is made of silicon.